

P-Channel Enhancement Mode MOSFET

TDM2301S

Features

- -20V/-1.5A ,
 $R_{DS(ON)} = 130m\Omega (typ.) @ V_{GS} = -4.5V$
 $R_{DS(ON)} = 170m\Omega (typ.) @ V_{GS} = -2.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)

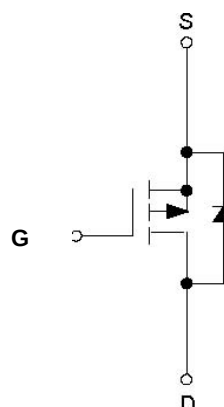
Applications

- Power Management in Notebook Computer , Portable Equipment and Battery Powered Systems.

Pin Description



Top View of SOT23-3L



P-Channel MOSFET

Ordering and Marking Information

TDM2301S □ □ □ □ Lead Free Code Handling Code Temp. Range Package Code	Package Code A: SOT23-3L Operating Junction Temp. Rang C: -55 to 150°C Handling Code TU:Tube TR:Tape & Reel Lead Free Code: L:Lead Free Device Blank:Original Device
TDM2301S M23 X	X:Date Code

Note: TECHCODE lead-free products contain molding compounds/die attach materials and 100% matte in plate termination finish; which are fully compliant with RoHS and compatible with both SnPb and lead-free soldering operations. TECHCODE lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J STD-020C for MSL classification at lead-free peak reflow temperature.

TECHCODE reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

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Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
VDSS	Drain-Source Voltage		-20	V
VGSS	Gate-Source Voltage		± 12	
ID*	Continuous Drain Current		-1.5	A
IDM*	300 μs Pulsed Drain Current	VGS=-4.5V	-6	
IS*	Diode Continuous Forward Current		-1	A
TJ	Maximum Junction Temperature		150	$^\circ\text{C}$
TSTG	Storage Temperature Range		-55 to 150	
PD*	Maximum Power Dissipation	TA=25 $^\circ\text{C}$	0.83	W
		TA=100 $^\circ\text{C}$	0.3	
R θ JA*	Thermal Resistance-Junction to Ambient		150	$^\circ\text{C/W}$

Note: *Surface Mounted on 1in² pad area, $t \leq 10\text{sec}$.Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

			TDM2301S			
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-16V , V _{GS} =0V T_J=85°C			-1 -30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-0.5	-0.6	-1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±12V, V _{DS} =0V			±100	nA
R _{DS(ON)} a	Drain-Source On-state Resistance	V _{GS} =-4.5V, I _{DS} =-1.5A		130	170	mΩ
		V _{GS} =-2.5V, I _{DS} =-0.6A		170	220	
V _{SD} a	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V		-0.7	-1.3	V
Gate Charge Characteristics b						
Q _g	Total Gate Charge	V _{DS} =-10V, V _{GS} =-4.5V, I _{DS} =-1A		5	7	nC
Q _{gs}	Gate-Source Charge			1.3		
Q _{gd}	Gate-Drain Charge			1.3		

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Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	TDM2301S			Unit
			Min.	Typ.	Max.	
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz		12		Ω
C _{iSS}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, Frequency=1.0MHz		350		PF
C _{oss}	Output Capacitance			75		
C _{rSS}	Reverse Transfer Capacitance			55		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-10V, R _L =10Ω, I _{DS} =-1A, V _{GEN} =-4.5V, R _G =6Ω		6	10	Ns
T _r	Turn-on Rise Time			8	12	
t _{d(OFF)}	Turn-off Delay Time			25	45	
T _f	Turn-off Fall Time			20	36	

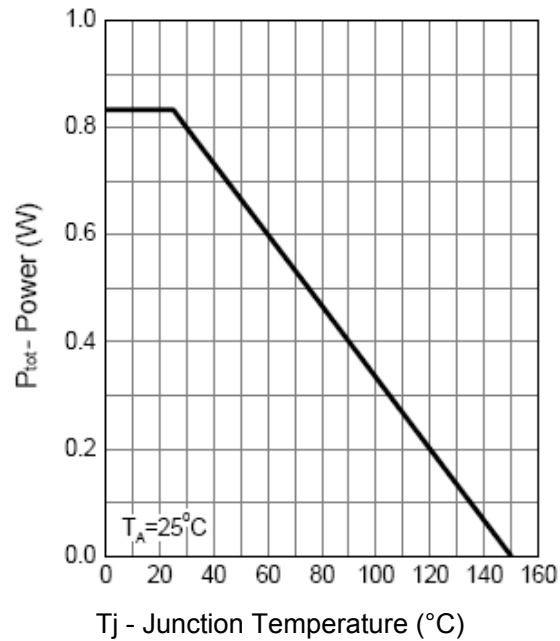
Notes:

a : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

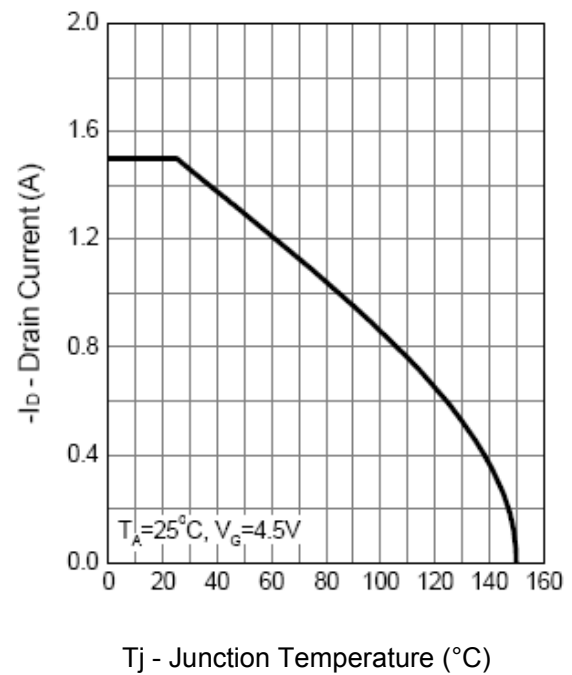
b : Guaranteed by design, not subject to production testing.

Typical Characteristics

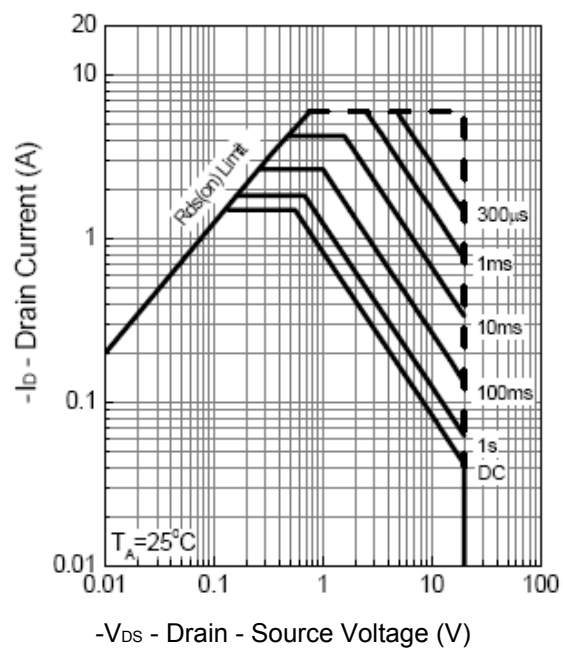
Power Dissipation



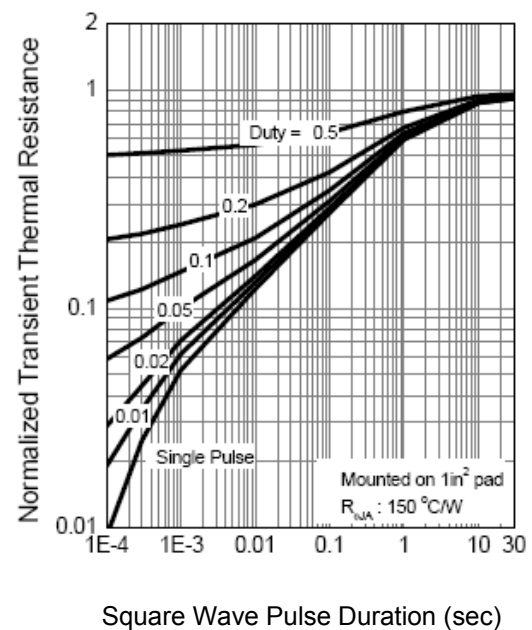
Drain Current



Safe Operation Area

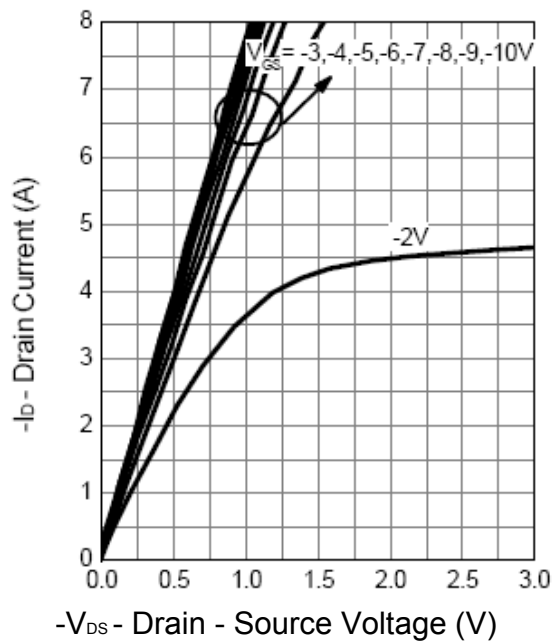


Thermal Transient Impedance

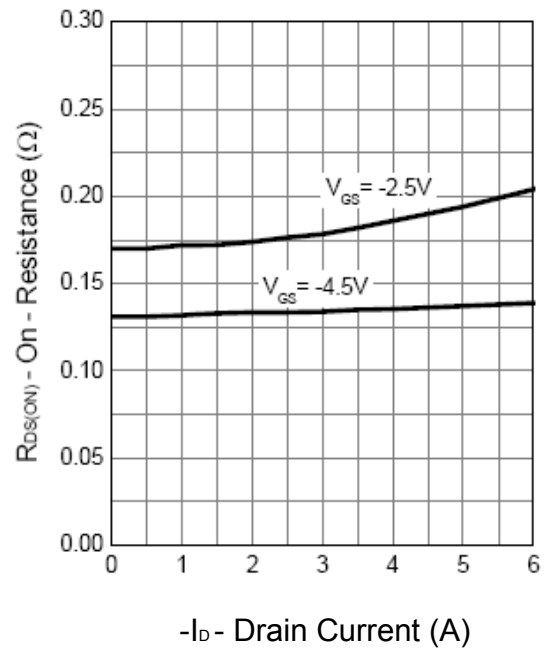


Typical Characteristics (Cont.)

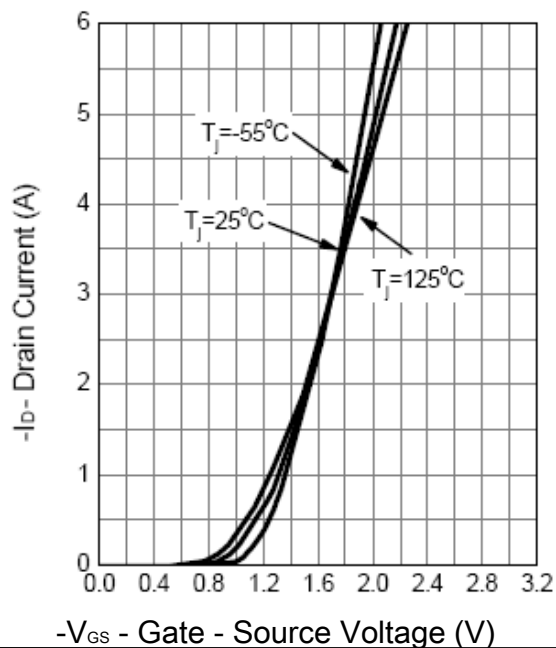
Output Characteristics



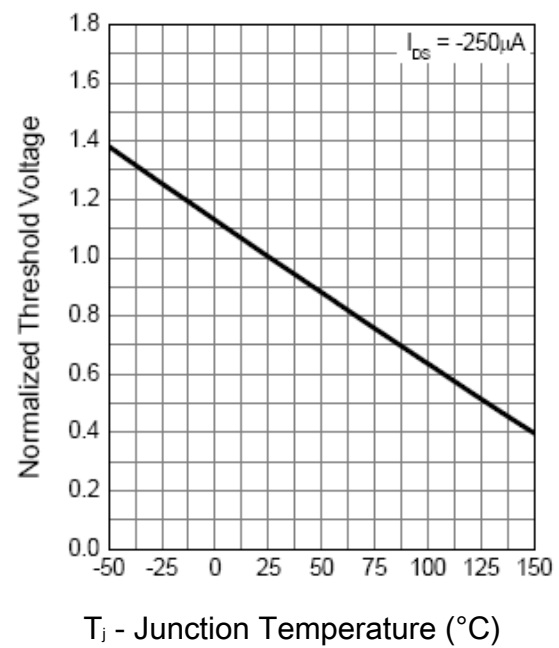
Drain-Source On Resistance



Transfer Characteristics

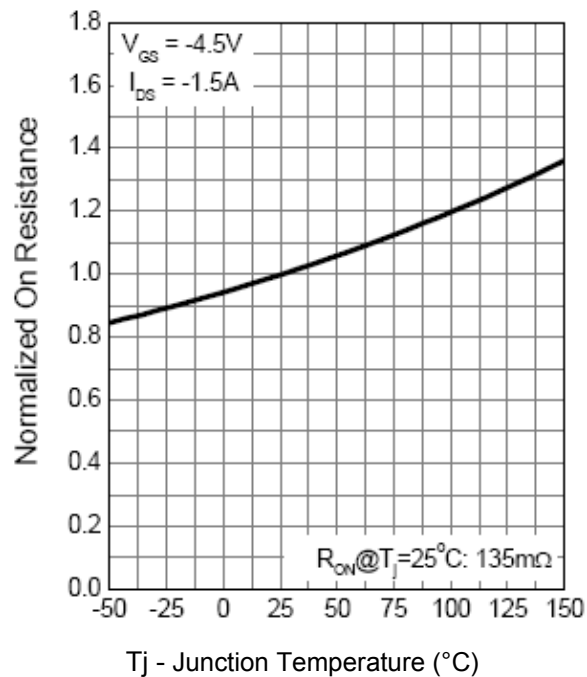


Gate Threshold Voltage

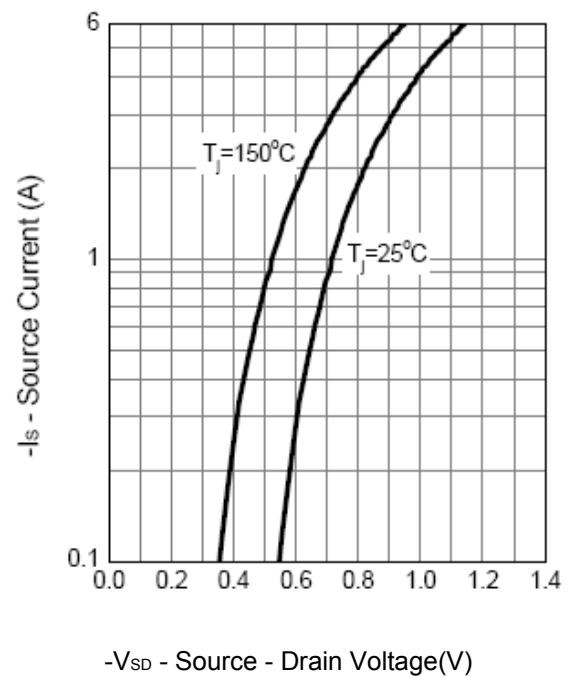


Typical Characteristics (Cont.)

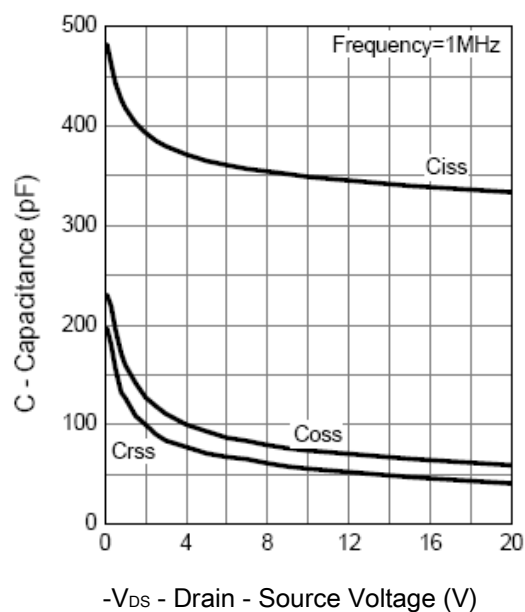
Drain-Source On Resistance



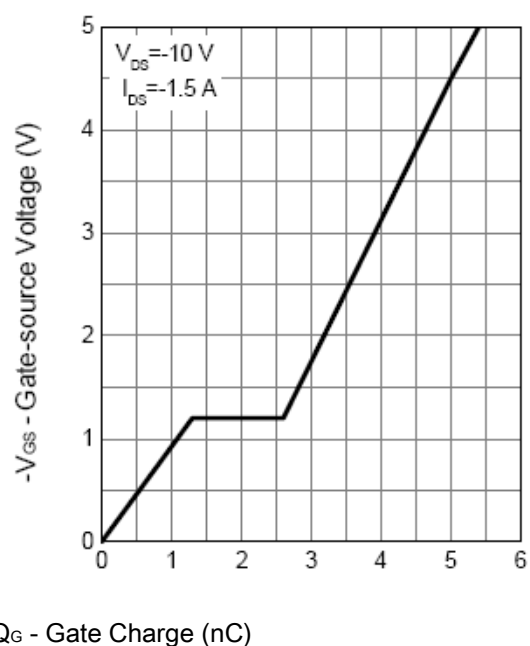
Source-Drain Diode Forward



Capacitance

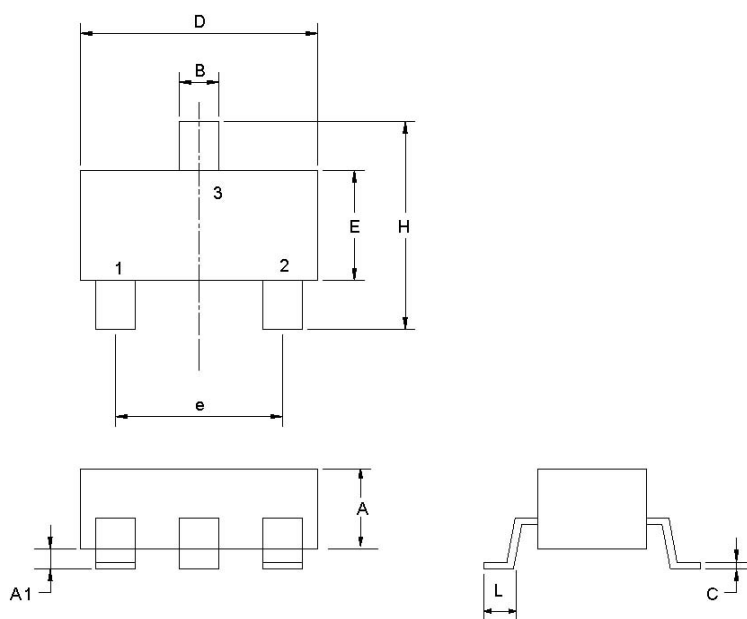


Gate Charge



Packaging Information

SOT23-3L



Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
B	0.35	0.51	0.014	0.020
C	0.10	0.25	0.004	0.010
D	2.70	3.10	0.106	0.122
E	1.40	1.80	0.055	0.071
e	1.90/2.1 BSC.		0.075/0.083 BSC.	
H	2.40	3.00	0.094	0.118
L	0.37		0.015	

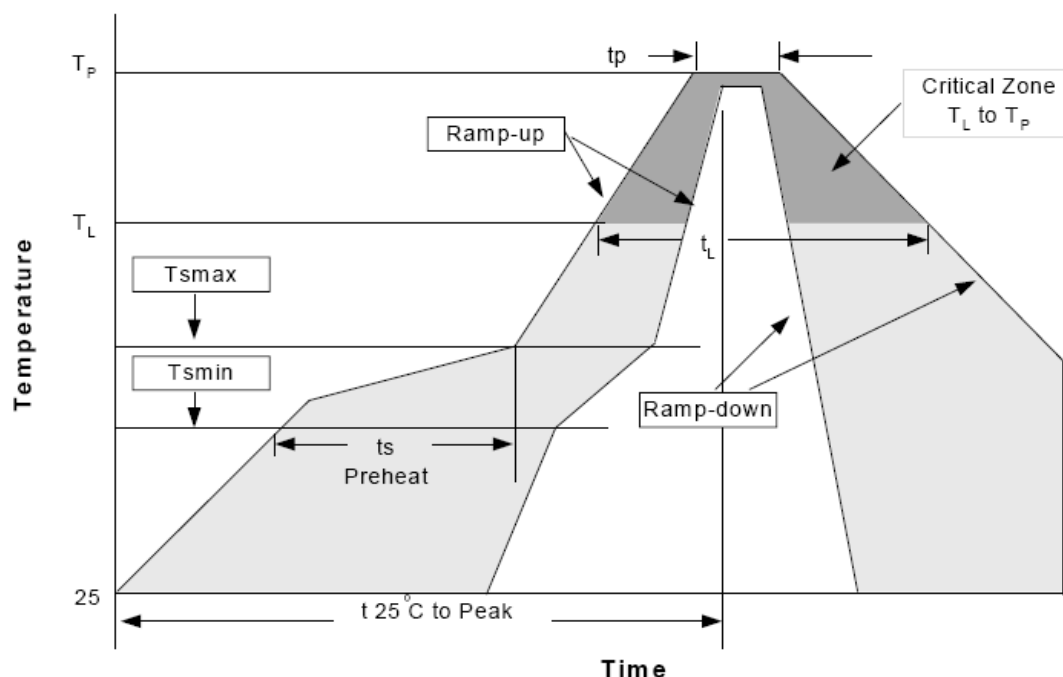
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Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly		Pb-Free Assembly	
	Large Body	Small Body	Large Body	Small Body
Average ramp-up rate (TL to TP)	3°C/second max.		3°C/second max.	
Preheat	100°C		150°C	
Temperature Min (Tsmmin)	150°C		200°C	
Temperature Max (Tsmmax)	60-120 seconds		60-180 seconds	
Time (min to max) (ts)	183°C		217°C	
Time maintained above:	60-150 seconds		60-150 seconds	
Temperature (TL)	225+0/-5°C		245+0/-5°C	
Time (tL)	240+0/-5°C		250+0/-5°C	
Peak/Classification Temperature (Tp)	10-30 seconds		20-40 seconds	
Time within 5°C of actual Peak Temperature (tp)	6°C/second max		6°C/second max	
Ramp-down Rate	6 minutes max		8 minutes max	
Time 25°C to Peak Temperature				

Notes: All temperatures refer to topside of the package .Measured on the body surface.

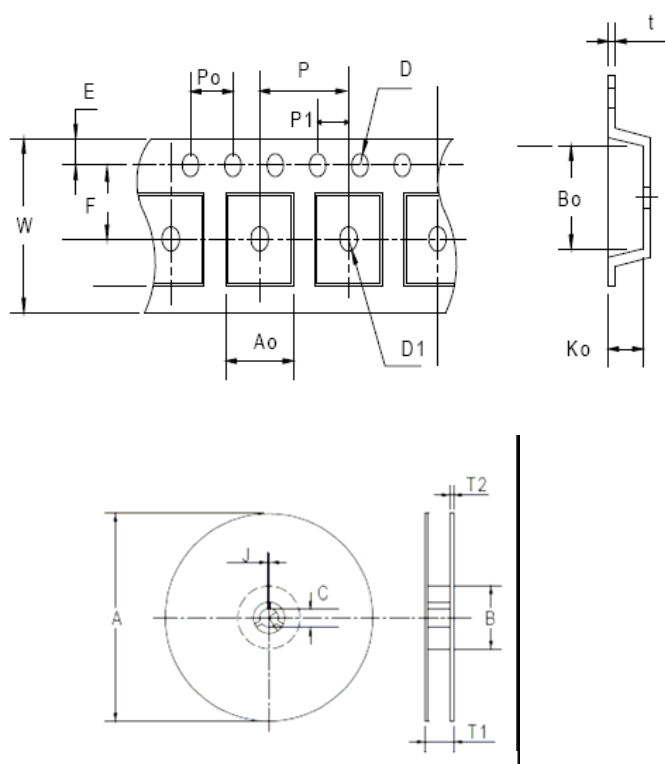
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Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Carrier Tape & Reel Dimensions



Application	A	B	C	J	T1	T2	W	P	E
SOT23-3L	178±1	60 ± 1.0	12.0	2.5 ± 0.15	9.0 ± 0.5	1.4	8.0+ 0.3 - 0.3	4.0	1.75
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	3.5 ± 0.05	1.5 +0.1	0.1MIN	4.0	2.0 ± 0.05	3.1	3.0	1.3	0.2±0.03

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
SOT 23-3L	8	5.3	3000